BT136S series D

# **GENERAL DESCRIPTION**

## **QUICK REFERENCE DATA**

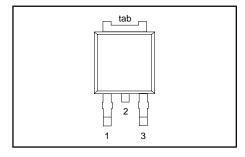
Passivated, sensitive gate triacs in a plastic envelope suitable for surface mounting, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>DRM</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	<b>600D</b> 600 4 25	V A A

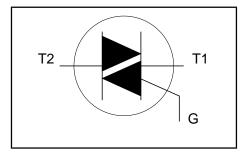
## **PINNING - SOT428**

PIN	DESCRIPTION
1	MT1
2	MT2
3	gate
tab	MT2

## **PIN CONFIGURATION**



## **SYMBOL**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-600</b> 600	\ \
$I_{T(RMS)} \\ I_{TSM}$	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 107  ^{\circ}\text{C}$ full sine wave; $T_{j} = 25  ^{\circ}\text{C}$ prior to surge	-	4	А
		t = 20 ms	-	25 27	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 16.7 ms t = 10 ms	-	3.1	A A <sup>2</sup> s
dl <sub>⊤</sub> /dt	Repetitive rate of rise of on-state current after	$I_{TM} = 6 \text{ A}; I_G = 0.2 \text{ A}; \\ dI_G/dt = 0.2 \text{ A}/\mu\text{s}$			
	triggering	T2+ G+	-	50	A/μs
		T2+ G-	-	50 50	A/μs
		T2- G- T2- G+	_	50 10	A/μs A/μs
l low	Peak gate current	12 01	_	2	ΙΑΙ
$V_{\rm GM}$	Peak gate voltage		-	5 5	V
$IP_{GM}$	Peak gate power		-		W
P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -	0.5 150 125	°C °C

BT136S series D

# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle pcb (FR4) mounted; footprint as in Fig.14	1 1 1	- - 75	3.0 3.7 -	K/W K/W K/W

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
			72+ G+	-	2.0	5	mΑ
		Τ	72+ G-	-	2.5	5 5	mΑ
			⁻2- G-	-	2.5	5	mΑ
			T2- G+	-	5.0	10	mΑ
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
			「2+ G+	-	1.6	10	mΑ
		-	「2+ G-	-	4.5	15	mΑ
			T2- G-	-	1.2	10	mΑ
			「2- G+	-	2.2	15	mΑ
l I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	1.2	10	mΑ
V <sub>T</sub>	On-state voltage	$I_T = 5 A$		-	1.4	1.70	V
V <sub>GT</sub>	Gate trigger voltage	$\begin{vmatrix} \dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A} \\ V_{D} = 400 \text{ V}; I_{T} = 0.1 \text{ A}; T_{i} = 125 ^{\circ}\text{C}$	_	-	0.7	1.5	V
		$ V_D  = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	C	0.25	0.4	-	V
$I_D$	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125 °C$		-	0.1	0.5	mA

## **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	-	5	-	V/μs
t <sub>gt</sub>	off-state voltage Gate controlled turn-on time	exponential waveform; $R_{GK} = 1 \text{ k}\Omega$ $I_{TM} = 6 \text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1 \text{ A}$ ; $dI_G/dt = 5 \text{ A}/\mu s$	-	2	-	μs

BT136S series D

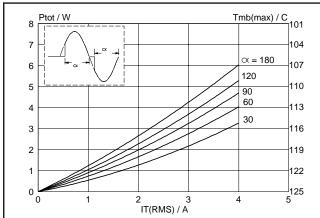


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

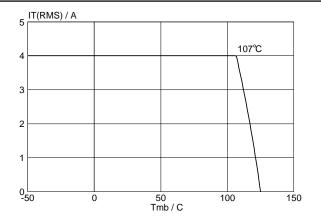


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

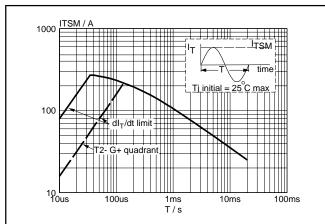


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

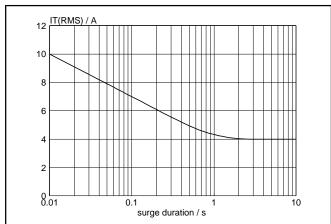


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 107$  °C.

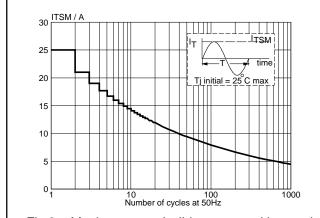


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

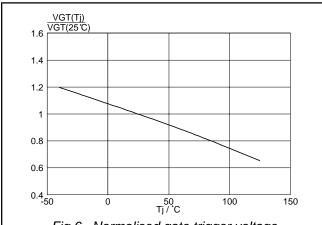
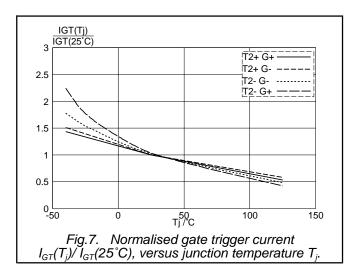


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_j$ .

# BT136S series D



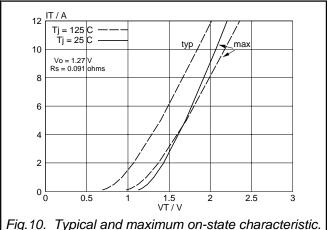


Fig. 10. Typical and maximum on-state characteristic.

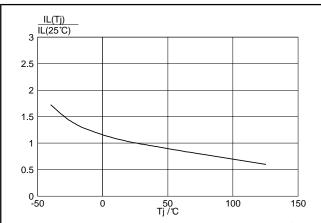


Fig.8. Normalised latching current  $I_L(T_j)/I_L(25^{\circ}\text{C})$ , versus junction temperature  $T_j$ .

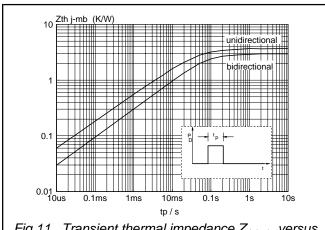


Fig.11. Transient thermal impedance  $Z_{th i-mb}$ , versus pulse width  $t_{\rm p}$ .

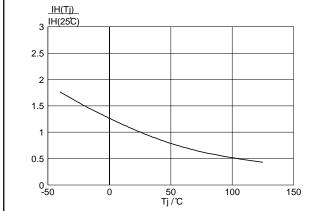


Fig.9. Normalised holding current  $I_H(T_i)/I_H(25^{\circ}\text{C})$ , versus junction temperature  $T_j$ .

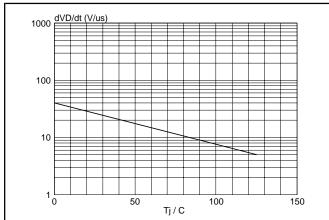
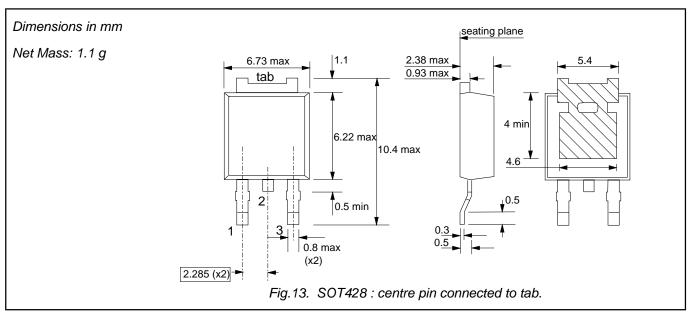


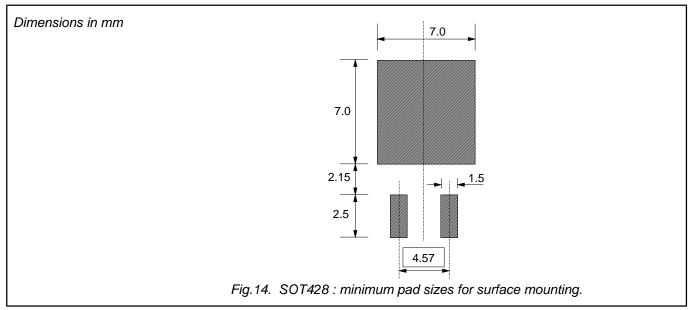
Fig.12. Typical, critical rate of rise of off-state voltage,  $dV_D/dt$  versus junction temperature  $T_{j\cdot}$ 

BT136S series D

## **MECHANICAL DATA**



## **MOUNTING INSTRUCTIONS**



### **Notes**

1. Plastic meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Triacs logic level

BT136S series D

### **DEFINITIONS**

DATA SHEET STATUS				
DATA SHEET STATUS <sup>1</sup>	PRODUCT STATUS <sup>2</sup>	DEFINITIONS		
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice		
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in ordere to improve the design and supply the best possible product		
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A		

### **Limiting values**

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

## **Application information**

Where application information is given, it is advisory and does not form part of the specification.

### © Philips Electronics N.V. 2001

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

<sup>1</sup> Please consult the most recently issued datasheet before initiating or completing a design.

**<sup>2</sup>** The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.